

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

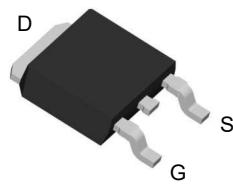
Product Summary



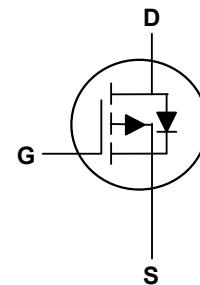
V_{DS}	-40	V
I_D	-20	A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	45	mΩ
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	58	mΩ

Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



TO-252 Top View



Absolute Maximum Ratings($T_A=25^\circ C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	-20	A
Pulsed Drain Current ²	I_{DM}	-80	A
Single Pulse Avalanche Energy ³	E_{AS}	18	mJ
Total Power Dissipation ⁴	P_D	27.8	W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	55	°C/W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	4.5	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}$, $I_D=-250\mu\text{A}$	-40	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-10\text{V}$, $I_D=-6\text{A}$	---	34	45	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}$, $I_D=-3\text{A}$	---	44	58	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D = -250\mu\text{A}$	-1.0	---	-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=-40\text{V}$, $V_{\text{GS}}=0\text{V}$	---	---	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Forward Transconductance	g_{fs}	$V_{\text{DS}}=-10\text{V}$, $I_D=-6\text{A}$	---	16	---	S
Total Gate Charge	Q_g	$V_{\text{DS}}=-20\text{V}$, $V_{\text{GS}}=-10\text{V}$, $I_D=-6\text{A}$	---	17	---	nC
Gate-Source Charge	Q_{gs}		---	4.2	---	
Gate-Drain Charge	Q_{gd}		---	3.7	---	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=-20\text{V}$, $V_{\text{GS}}=-10\text{V}$, $R_G=3\Omega$, $I_D=-6\text{A}$	---	5.9	---	ns
Rise Time	T_r		---	7.1	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	25	---	
Fall Time	T_f		---	8.2	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=-20\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	1080	---	pF
Output Capacitance	C_{oss}		---	87	---	
Reverse Transfer Capacitance	C_{rss}		---	77	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ¹	I_s		---	---	-20	A
Diode Forward Voltage ²	V_{SD}	$V_{\text{GS}}=0\text{V}$, $I_s=-6\text{A}$, $T_J=25^\circ\text{C}$	---	---	-1.2	V

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{\text{DD}}=-25\text{V}$, $V_{\text{GS}}=-10\text{V}$, $L=0.1\text{mH}$, $I_{\text{AS}}= -19\text{A}$.
- 4.The power dissipation is limited by 150°C junction temperature

Typical Characteristics

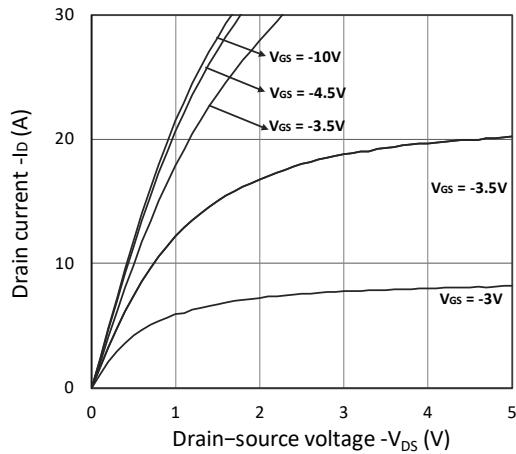


Figure 1. Output Characteristics

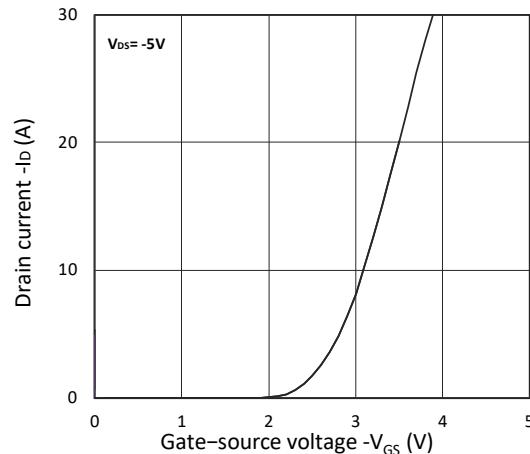


Figure 2. Transfer Characteristics

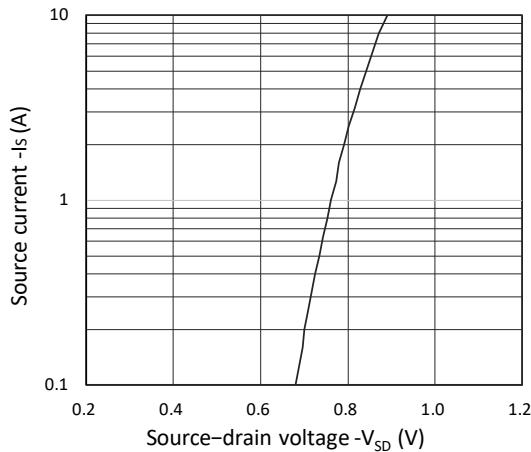


Figure 3. Forward Characteristics of Reverse

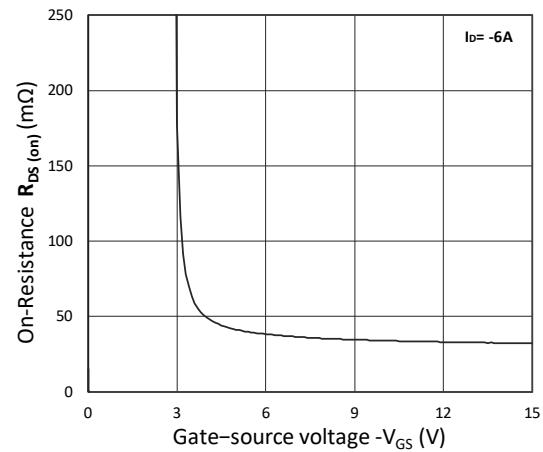


Figure 4. $R_{DS(on)}$ vs. V_{GS}

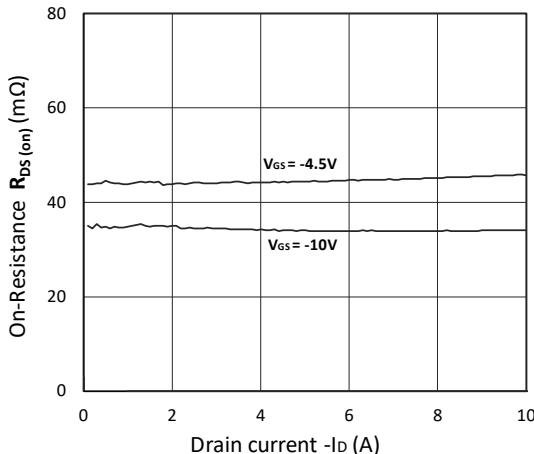


Figure 5. $R_{DS(on)}$ vs. I_D

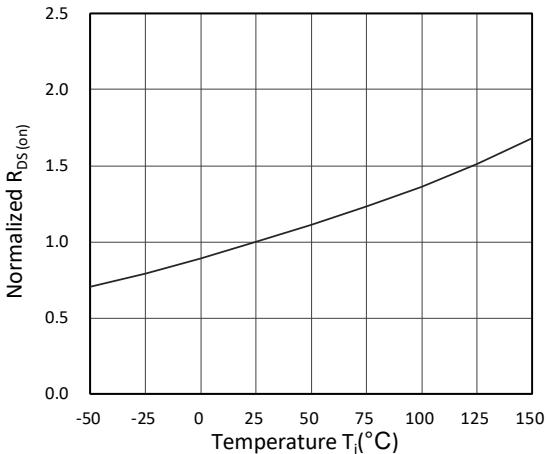


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

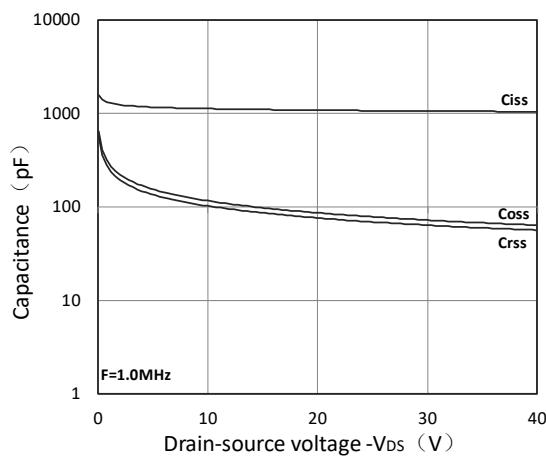


Figure 7. Capacitance Characteristics

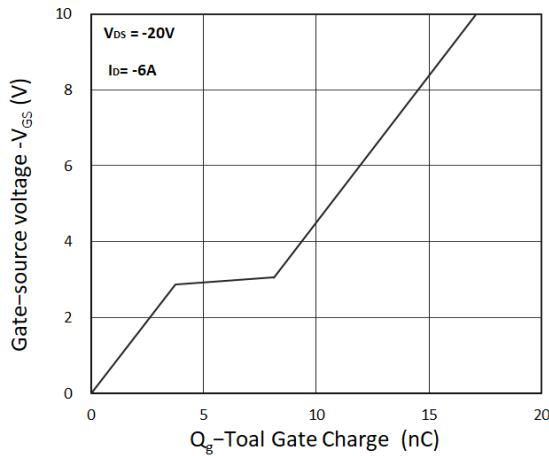


Figure 8. Gate Charge Characteristics

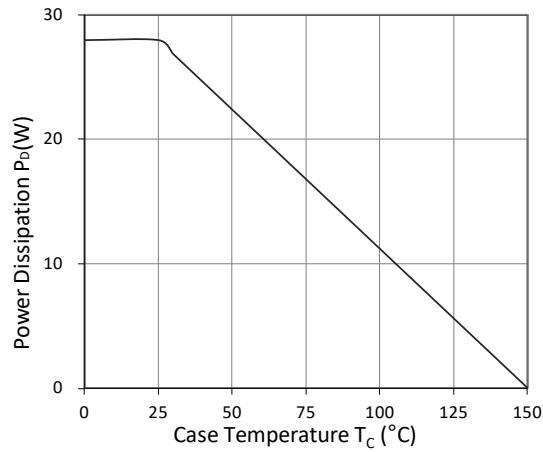


Figure 9. Power Dissipation

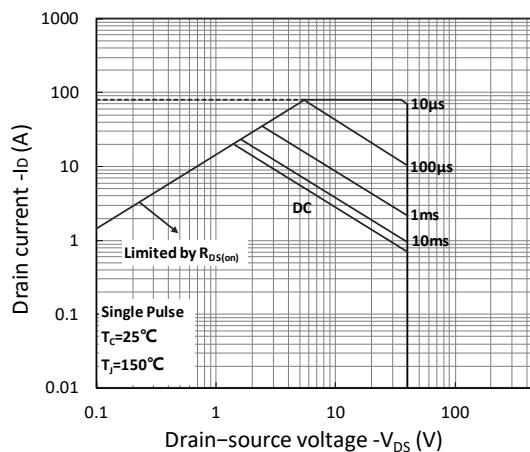


Figure 10. Safe Operating Area

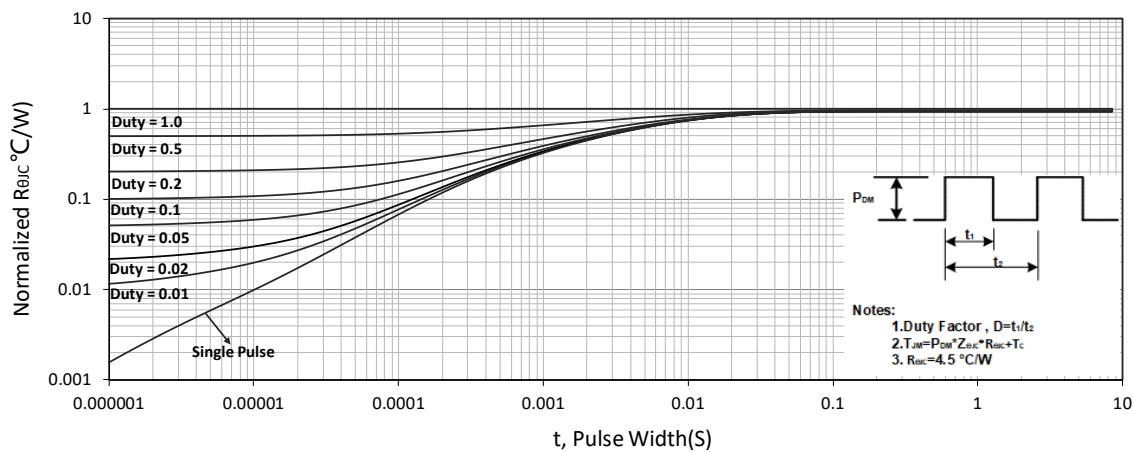
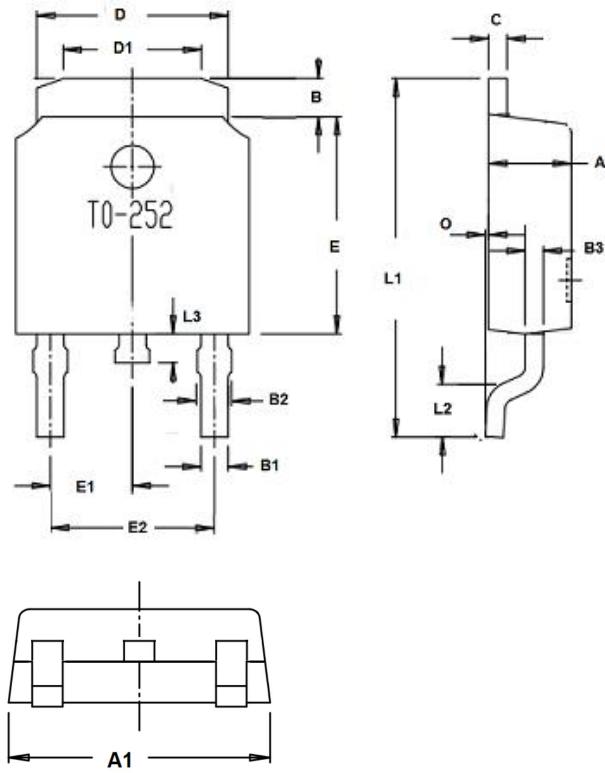


Figure 11. Normalized Maximum Transient Thermal Impedance

TO-252 Package Outline Dimensions

Dim.	Min.	Max.
A	2.1	2.5
A1	6.3	6.9
B	0.96	1.42
B1	0.74	0.86
B2	0.74	0.94
C	Typ0.5	
D	5.33	5.53
D1	3.65	4.05
E	6.0	6.2
E1	Typ2.29	
E2	Typ4.58	
O	0	0.15
L1	9.9	10.5
L2	Typ1.65	
L3	0.6	1.0
All Dimensions in millimeter		